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Toward spin-based Magneto Logic Gate in Graphene HUA WEN,
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has emerged as a leading candidate for spintronic applications due to its long spin
diffusion length at room temperature. A universal magnetologic gate (MLG) based
on spin transport in graphene has been recently proposed as the building block of
a logic circuit which could replace the current CMOS technology. This MLG has
five ferromagnetic electrodes contacting a graphene channel and can be considered
as two three-terminal XOR logic gates. Here we demonstrate this XOR logic gate
operation in such a device. This was achieved by systematically tuning the injection
current bias to balance the spin polarization efficiency of the two inputs, and offset
voltage in the detection circuit to obtain binary outputs. The output is a current
which corresponds to different logic states: zero current is logic ‘0’, and nonzero
current is logic ‘1’. We find improved performance could be achieved by reducing
device size and optimizing the contacts.

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